

SILICON NPN EPITAXIAL PLANAR TRANSISTOR

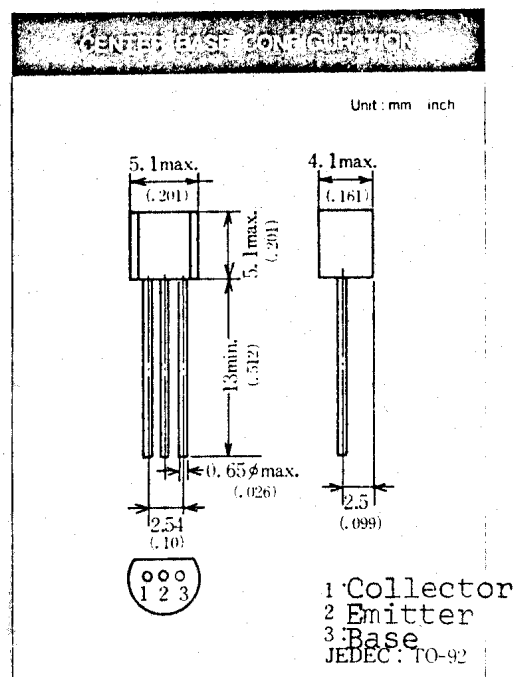
APPLICATION:

- Mixer, Oscillator

FEATURES:

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Collector-Base Voltage (V _{CB0})	25V
Collector-Emitter Voltage (V _{CEO})	20V
Emitter-Base Voltage (V _{EB0})	3V
Collector Current (I _C)	15mA
Peak Collector Current (I _{CM})	150mA
Power Dissipation (P _C)	150mW
Junction Temperature (T _j)	125°C
Storage Temperature (T _{stg})	



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =2mA, I _B =0	25			V
Collector Cutoff Current	I _{CB0}	V _{CB} =10V, I _E =0			1	μA
Collector Cutoff Current	I _{CE}	V _{CE} =25V, I _B =0			100	μA
DC Current Gain	-h _{FE1}	V _{CE} =10V, I _C =3mA	20	50		
Collector-Emitter Saturation Voltage	V _{CE(sat)}					V
Gain-Bandwidth Product	f _T	V _{CB} =10V, I _E =3mA	600			MHz
Collector Capacitance	C _{ob}	V _{CB} =10V, I _E =1mA, f=10.7MHz	0.5		0.6	pF

h_{FE} CLASSIFICATION

Class	O	P	Q	R	S	T
h _{FE}						

The device specifications are subject to change for improvement without prior notice.